

## IN THE CLAIMS

Each claim of the application is set forth below with a parenthetical notation immediately following the claim number indicating the claim status. The Examiner's entry of the claim amendments under Section 1.121 is respectfully requested.

1. (ORIGINAL) A physical vapor deposition chamber for depositing material on a wafer, comprising:

a chuck for supporting the wafer, wherein the chuck comprises an upper surface and sidewalls extending downwardly therefrom;

a pedestal cover overlying the upper surface and extending beyond the sidewalls, the pedestal cover defining a peripheral circumferential groove therein; and

wherein the wafer is positionable over the pedestal cover.

2. (ORIGINAL) The physical vapor deposition chamber of claim 1 wherein the pedestal cover further comprises a plurality of pads on an upper surface thereof, such that the wafer may be disposed on the plurality of pads.

3. (ORIGINAL) The physical vapor deposition chamber of claim 1 further comprising an aluminum target for depositing aluminum on the wafer.

4. (WITHDRAWN) A physical vapor deposition chamber for depositing material on a wafer, comprising:

a chuck comprising an upper surface for supporting the wafer;

a pedestal cover overlying the upper surface and having downwardly directed sidewalls defining an opening;

wherein the chuck is disposed within the opening and the wafer is positionable over the pedestal cover extending beyond the sidewalls.

5. (WITHDRAWN) The physical vapor deposition chamber of claim 4 wherein the pedestal cover further comprises a plurality of pads on an upper surface of the pedestal cover, such that the wafer may be disposed on the plurality of pads.

6. (ORIGINAL) A pedestal cover for a material deposition process, wherein during the process material is deposited on a semiconductor wafer supported by a chuck, and wherein the pedestal cover is disposed intermediate the chuck and the wafer, the cover comprising;

a disk defining a peripheral circumferential trench therein and downwardly directed sidewalls extending from a bottom surface thereof, the sidewalls further defining an opening; and

wherein the wafer may be positioned over the disk during the material deposition process; and

wherein the chuck may be disposed within the opening during the material deposition process.

7. (ORIGINAL) The pedestal cover of claim 6 further comprising a plurality of pads on an upper surface of the disk, such that the wafer may be disposed on the plurality of pads during the material deposition process.

8. (ORIGINAL) The pedestal cover of claim 6 wherein a material of the pedestal cover comprises stainless steel.

9. (ORIGINAL) The pedestal cover of claim 6 wherein the material of the material deposition process is deposited on the pedestal cover during the material deposition process and is removable therefrom.

10. (WITHDRAWN) A pedestal cover for a material deposition process, wherein during the process material is deposited on a semiconductor wafer supported by a chuck, and wherein the pedestal cover is disposed intermediate the chuck and the wafer, the cover comprising;

a disk comprising a support member and sidewalls extending downwardly from a bottom surface of the support member, wherein the sidewalls define an opening;

such that the chuck may be disposed within the opening during the material deposition process; and

such that the wafer may be disposed overlying the support member and extending beyond the sidewalls during the material deposition process.

11. (WITHDRAWN) The pedestal cover of claim 10 further comprising a plurality of pads on an support member, such that the wafer is positionable on the plurality of pads during the material deposition process.

12. (WITHDRAWN) The pedestal cover of claim 10 wherein a material of the pedestal cover comprises stainless steel.

13. (WITHDRAWN) The pedestal cover of claim 10 wherein the material of the material deposition process is deposited on the pedestal cover during the material deposition process and is removable therefrom.